

QSZ1

Transistors

# General purpose transistor

## QSZ1

A 2SB1690 and a 2SD2653 are housed independently in a TSMT5 package.

### ●Applications

DC / DC converter  
Motor driver

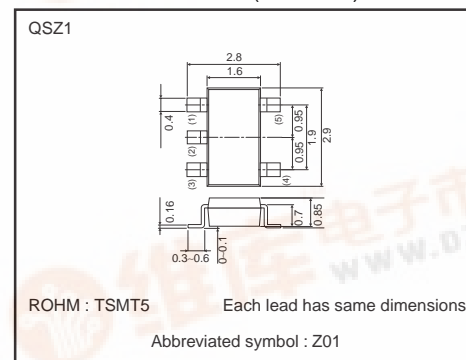
### ●Features

- 1) Low  $V_{CE(sat)}$
- 2) Small package

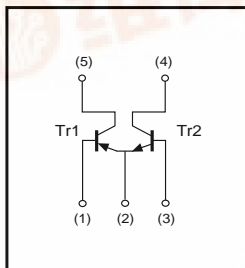
### ●Structure

Silicon epitaxial planar transistor

### ●External dimensions (Unit : mm)



### ●Equivalent circuit



### ●Packaging specifications

Type	QSZ1
Package	TSMT5
Marking	Z01
Code	TR
Basic ordering unit(pieces)	3000

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## ●Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	−15	V
Collector-emitter voltage	V <sub>CEO</sub>	−12	V
Emitter-base voltage	V <sub>EB0</sub>	−6	V
Collector current	I <sub>C</sub>	−2	A
	I <sub>CP</sub>	−4	A *1
Collector power dissipation	P <sub>C</sub>	500	mW/Total *2
		1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	−55 to +150	°C

\*1 Single pulse Pw=1ms.

\*2 Each terminal mounted on a recommended land.

\*3 Mounted on a 25mm×25mm×0.8mm ceramic substrate.

Tr2

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	15	V
Collector-emitter voltage	V <sub>CEO</sub>	12	V
Emitter-base voltage	V <sub>EB0</sub>	6	V
Collector current	I <sub>C</sub>	2	A
	I <sub>CP</sub>	4	A *1
Power dissipation	P <sub>C</sub>	500	mW/Total *2
		1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	T <sub>J</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	−55 to +150	°C

\*1 Single pulse Pw=1ms.

\*2 Each terminal mounted on a recommended land.

\*3 Mounted on a 25mm×25mm×0.8mm ceramic substrate.

## ●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	−15	−	−	V	I <sub>C</sub> =−10μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	−12	−	−	V	I <sub>C</sub> =−1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	−6	−	−	V	I <sub>E</sub> =−10μA
Collector cutoff current	I <sub>CB0</sub>	−	−	−100	nA	V <sub>CB</sub> =−15V
Emitter cutoff current	I <sub>EB0</sub>	−	−	−100	nA	V <sub>EB</sub> =−6V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	−	−120	−180	mV	I <sub>C</sub> =−1mA, I <sub>B</sub> =−50mA
DC current transfer ratio	h <sub>FE</sub>	270	−	680	−	V <sub>CE</sub> =−2V, I <sub>C</sub> =−200mA *
Transition frequency	f <sub>T</sub>	−	360	−	MHz	V <sub>CE</sub> =−2V, I <sub>E</sub> =200mA, f=100MHz *
Output capacitance	C <sub>ob</sub>	−	15	−	pF	V <sub>CB</sub> =−10V, I <sub>E</sub> =0mA, f=1MHz

\* Pulsed

Tr2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	15	−	−	V	I <sub>C</sub> =10μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	12	−	−	V	I <sub>C</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	6	−	−	V	I <sub>E</sub> =10μA
Collector cutoff current	I <sub>CB0</sub>	−	−	100	nA	V <sub>CB</sub> =15V
Emitter cutoff current	I <sub>EB0</sub>	−	−	100	nA	V <sub>EB</sub> =6V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	−	90	180	mV	I <sub>C</sub> =1A, I <sub>B</sub> =50mA
DC current gain	h <sub>FE</sub>	270	−	680	−	V <sub>CE</sub> =2V, I <sub>C</sub> =200mA *
Transition frequency	f <sub>T</sub>	−	360	−	MHz	V <sub>CE</sub> =2V, I <sub>E</sub> =−200mA, f=100MHz *
Corrector output capacitance	C <sub>ob</sub>	−	20	−	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz

\* Pulsed

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## ●Electrical characteristic curves

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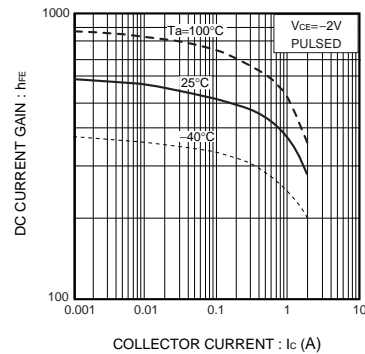


Fig.1 DC current gain vs. collector current

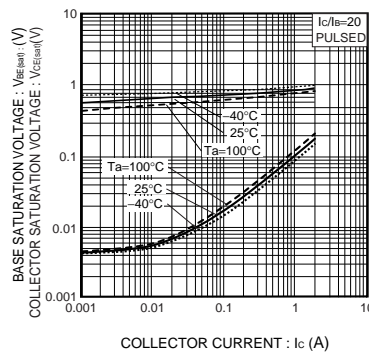


Fig.2 Collector-emitter saturation voltage vs. collector current

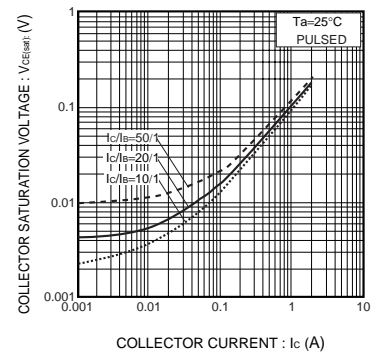


Fig.3 Collector-emitter saturation voltage vs. collector current

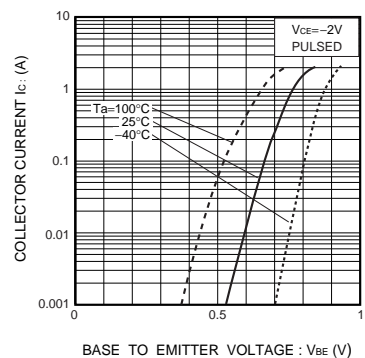


Fig.4 Grounded emitter propagation characteristics

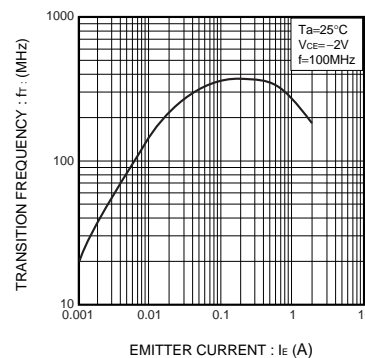


Fig.5 Gain bandwidth product vs. emitter current

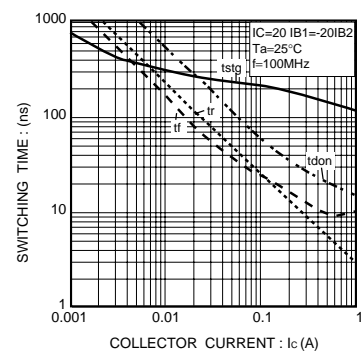


Fig.6 Switching time

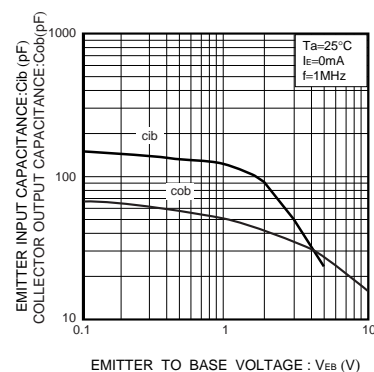


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

# Transistors

Tr2

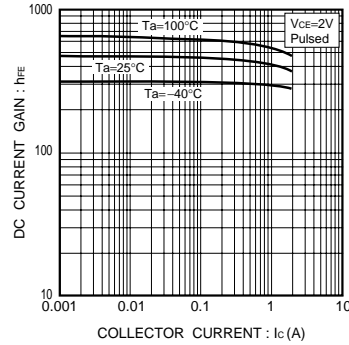


Fig.8 DC current gain vs. collector current

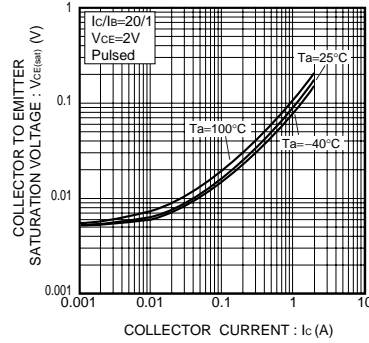


Fig.9 Base-emitter saturation voltage vs. collector current

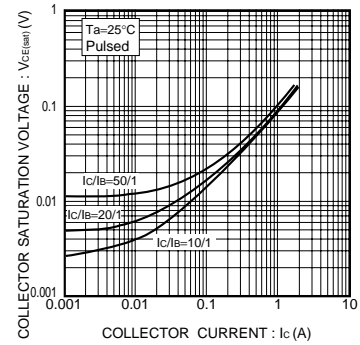


Fig.10 Collector-emitter saturation voltage vs. collector current

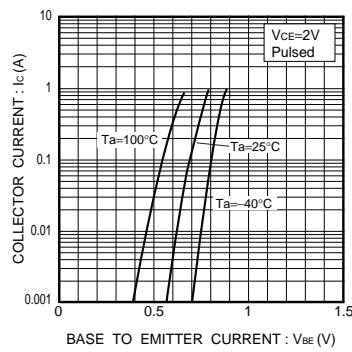


Fig.11 Grounded emitter propagation characteristics

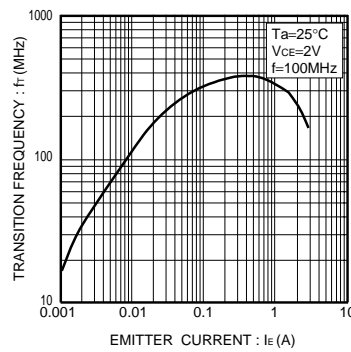


Fig.12 Gain bandwidth product vs. emitter current

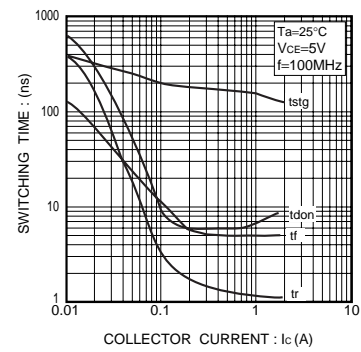


Fig.13 Switching time

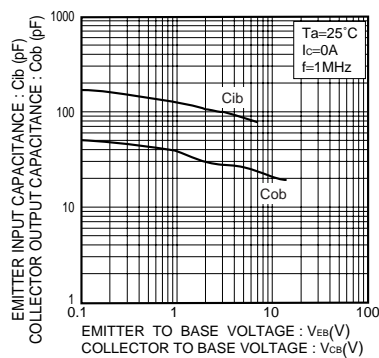


Fig.14 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

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